BUK9MGP-55PTS

Dual TrenchPLUS logic level FET

Rev. 01 — 14 May 2009 Product data sheet

1. Product profile

1.1 General description

Dual N-channel enhancement mode field-effect power transistor in SO20. Device is manufactured using NXP High-Performance (HPA) TrenchPLUS technology, featuring very low on-state resistance, integrated current sensing transistors and over temperature protection diodes.

1.2 Features and benefits

- Integrated current sensors
- Integrated temperature sensors

1.3 Applications

- Lamp switching
- Motor drive systems
- Power distribution
- Solenoid drivers

1.4 Quick reference data

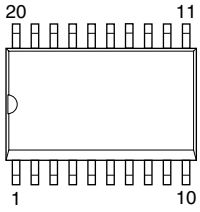
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics, FET1						
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 10 A; T_j = 25 °C; see Figure 23; see Figure 25	-	8.6	10	mΩ
I_D/I_{sense}	ratio of drain current to sense current	T_j = 25 °C; V_{GS} = 5 V; see Figure 27	8100	9000	9900	A/A
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 250 µA; T_j = 25 °C	55	-	-	V
Static characteristics, FET2						
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; see Figure 24; see Figure 26	-	21.3	25	mΩ
I_D/I_{sense}	ratio of drain current to sense current	T_j = 25 °C; V_{GS} = 5 V; see Figure 28	5910	6570	7227	A/A
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 250 µA; T_j = 25 °C	55	-	-	V

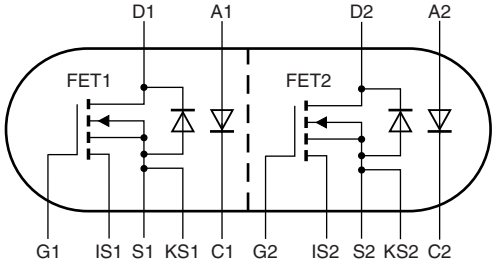
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G1	gate 1		
2	IS1	current sense 1		
3	D1	drain 1		
4	A1	anode 1		
5	C1	cathode 1		
6	G2	gate 2		
7	IS2	current sense 2		
8	D2	drain 2		
9	A2	anode 2		
10	C2	cathode 2		
11	D2	drain 2		
12	KS2	Kelvin source 2		
13	S2	source 2		
14	S2	source 2		
15	D2	drain 2		
16	D1	drain 1		
17	KS1	Kelvin source 1		
18	S1	source 1		
19	S1	source 1		
20	D1	drain 1		



SOT163-1
(SO20)



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3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9MGP-55PTS	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Limiting values, FET1						
V_{DS}	drain-source voltage	25 °C < T_j < 150 °C		-	55	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ; 25 °C < T_j < 150 °C		-	55	V
V_{GS}	gate-source voltage			-15	15	V
I_D	drain current	T_{sp} = 25 °C; V_{GS} = 5 V; see Figure 3; see Figure 7;	[1][2]	-	16.9	A
		T_{sp} = 100 °C; V_{GS} = 5 V; see Figure 3;	[1][2]	-	10.7	A
I_{DM}	peak drain current	T_{sp} = 25 °C; t_p ≤ 10 µs; pulsed; see Figure 7		-	349	A
P_{tot}	total power dissipation	T_{sp} = 25 °C; see Figure 1		-	5.2	W
T_{stg}	storage temperature			-55	150	°C
T_j	junction temperature			-55	150	°C
$V_{isol(FET-TSD)}$	FET to temperature sense diode isolation voltage			-	100	V
Limiting values, FET2						
V_{DS}	drain-source voltage	25 °C < T_j < 150 °C		-	55	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ; 25 °C < T_j < 150 °C		-	55	V
V_{GS}	gate-source voltage			-15	15	V
I_D	drain current	T_{sp} = 25 °C; V_{GS} = 5 V; see Figure 4; see Figure 8;	[1][2]	-	9.16	A
		T_{sp} = 100 °C; V_{GS} = 5 V; see Figure 4;	[1][2]	-	5.8	A
I_{DM}	peak drain current	T_{sp} = 25 °C; t_p ≤ 10 µs; pulsed; see Figure 8		-	148	A
P_{tot}	total power dissipation	T_{sp} = 25 °C; see Figure 2		-	3.9	W
T_{stg}	storage temperature			-55	150	°C
T_j	junction temperature			-55	150	°C
$V_{isol(FET-TSD)}$	FET to temperature sense diode isolation voltage			-	100	V
Source-drain diode, FET1						
I_S	source current	T_{sp} = 25 °C;	[1][2]	-	7.3	A
I_{SM}	peak source current	t_p ≤ 10 µs; pulsed; T_{sp} = 25 °C		-	349	A
Source-drain diode, FET2						
I_S	source current	T_{sp} = 25 °C;	[1][2]	-	5.5	A
I_{SM}	peak source current	t_p ≤ 10 µs; pulsed; T_{sp} = 25 °C		-	148	A
Avalanche ruggedness, FET1						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 16.9 A; V_{sup} ≤ 55 V; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; see Figure 5;	[3][4][5]	-	929	mJ
Avalanche ruggedness, FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 9.16 A; V_{sup} ≤ 55 V; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; see Figure 6;	[3][4][5]	-	360	mJ

Table 4. Limiting values *...continued*

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Electrostatic discharge, FET1					
V_{ESD}	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 kΩ; pins 3, 16 and 20 to pins 1, 2, 17, 18 and 19 shorted	-	4	kV
		HBM; C = 100 pF; R = 1.5 kΩ; all pins	-	0.15	kV
Electrostatic discharge, FET2					
V_{ESD}	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 kΩ; pins 8, 11 and 15 to pins 6, 7, 12, 13 and 14 shorted	-	4	kV
		HBM; C = 100 pF; R = 1.5 kΩ; all pins	-	0.15	kV

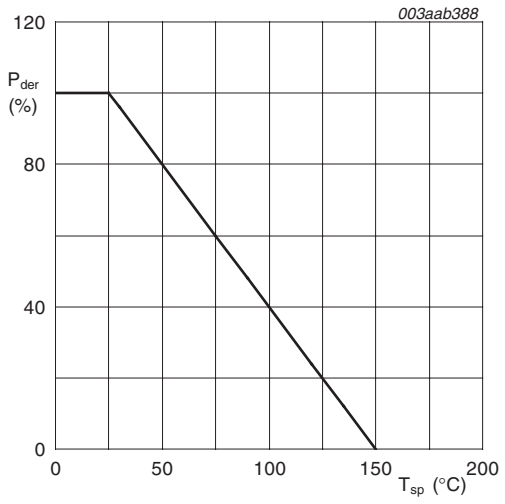
[1] Single device conducting.

[2] Current is limited by chip power dissipation rating.

[3] Single-pulse avalanche rating limited by maximum junction temperature of 150 °C.

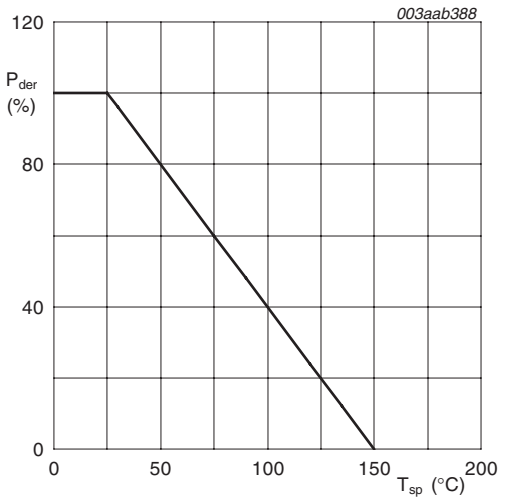
[4] Repetitive rating defined in avalanche rating figure.

[5] Refer to application note AN10273 for further information.



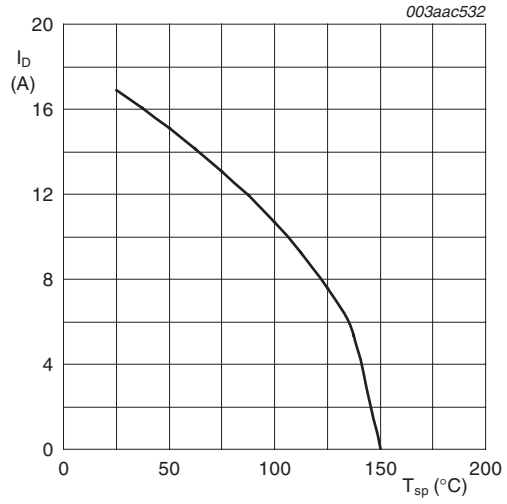
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature, FET1



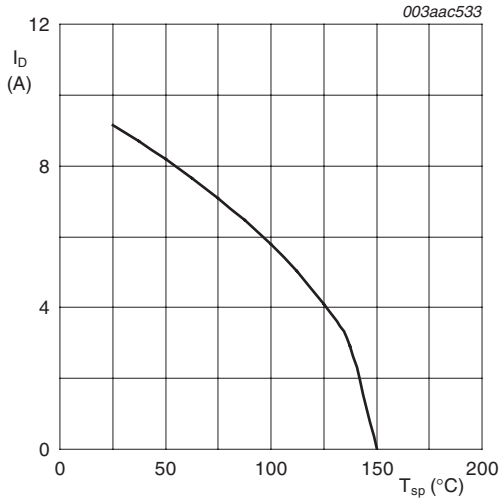
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of solder point temperature, FET2



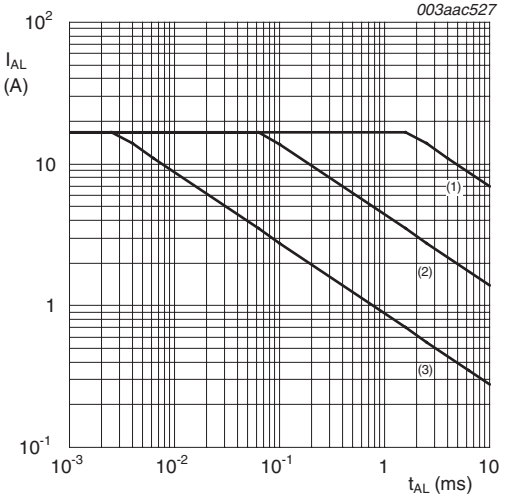
$V_{GS} \geq 5V$

Fig 3. Continuous drain current as a function of solder point temperature, FET1.



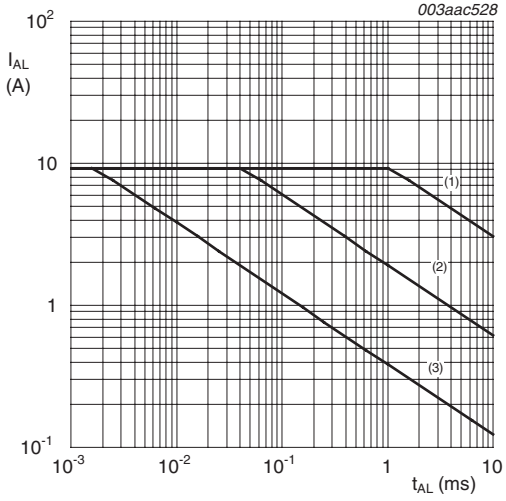
$V_{GS} \geq 5V$

Fig 4. Continuous drain current as a function of solder point temperature, FET2.



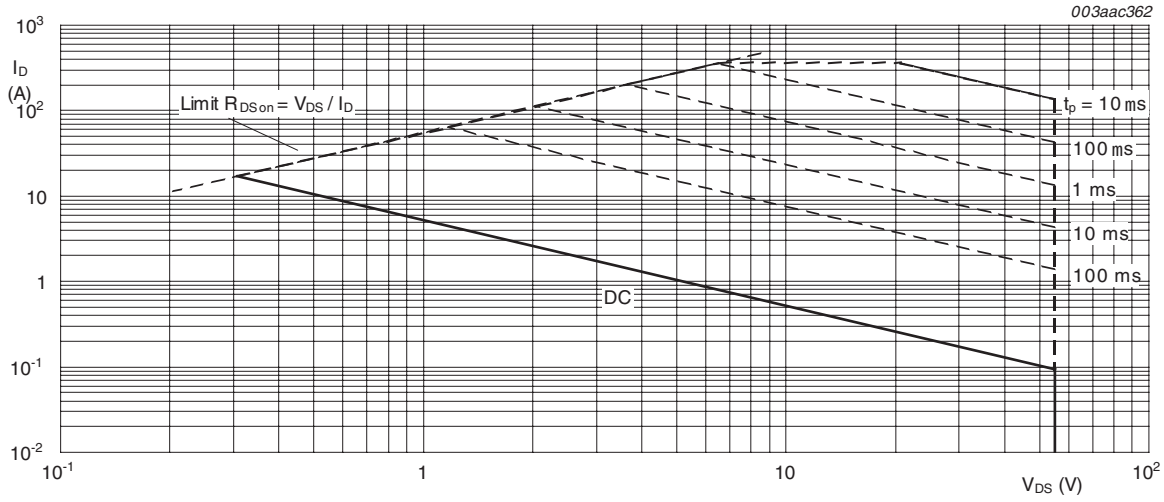
(1) Single-pulse; $T_j = 25\,°C$.
(2) Single-pulse; $T_j = 150\,°C$.
(3) Repetitive.

Fig 5. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1



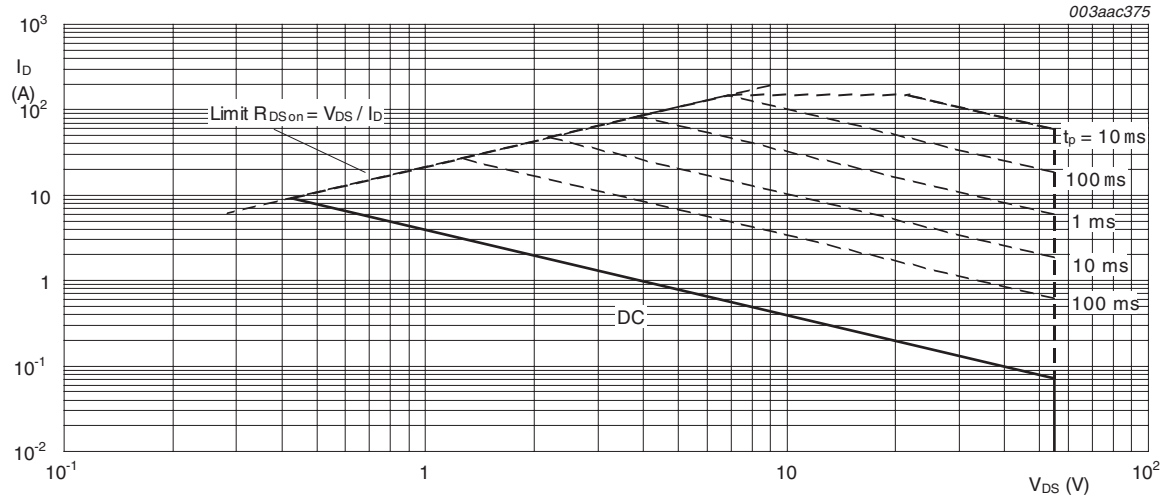
(1) Single-pulse; $T_j = 25\,°C$.
(2) Single-pulse; $T_j = 150\,°C$.
(3) Repetitive.

Fig 6. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET2



$T_{sp} = 25\,°C; I_{DM}$ is single pulse

Fig 7. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET1.



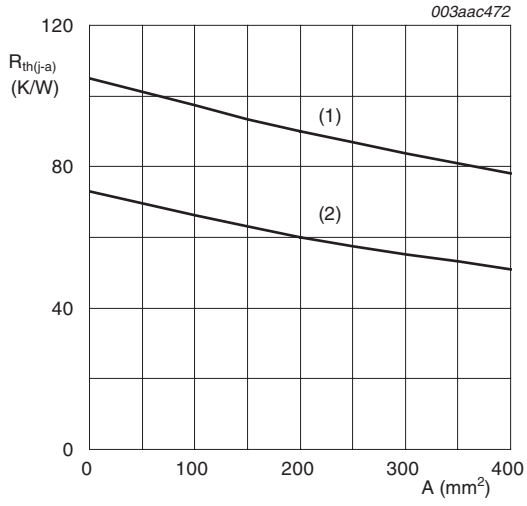
$T_{sp} = 25\,°C; I_{DM}$ is single pulse

Fig 8. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET2

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	FET1	-	-	24	K/W
		FET2	-	-	32	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on printed-circuit board; Both channel conducting; zero heat sink area; see Figure 9; see Figure 10	-	73	-	K/W
		mounted on printed-circuit board; Both channel conducting; 200 mm^2 copper heat sink area; see Figure 9; see Figure 11	-	60	-	K/W
		mounted on printed-circuit board; Both channel conducting; 400 mm^2 copper heat sink area; see Figure 9; see Figure 12	-	51	-	K/W
		mounted on printed-circuit board; One channel conducting; zero heat sink area; see Figure 9; see Figure 10	-	105	-	K/W
		mounted on printed-circuit board; One channel conducting; 200 mm^2 copper heat sink area; see Figure 9; see Figure 11	-	90	-	K/W
		mounted on printed-circuit board; One channel conducting; 400 mm^2 copper heat sink area; see Figure 9; see Figure 12	-	78	-	K/W



(1) One channel conducting dissipating 500mW.
(2) Both channels conducting each dissipating 500mW.
Zero air flow

Fig 9. Thermal resistance from junction to ambient as a function of printed-circuit board (PCB) heat sink area

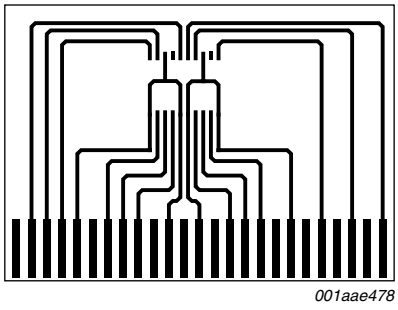


Fig 10. PCB used for thermal tests; zero heat sink area

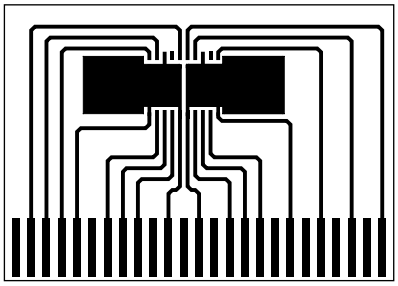


Fig 11. PCB used for thermal tests; heat sink area 200 mm²

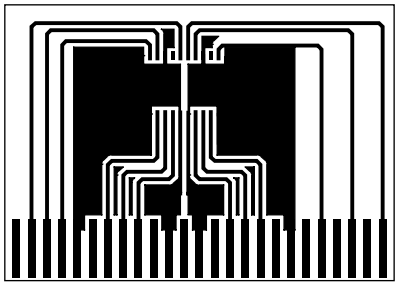


Fig 12. PCB used for thermal tests; heat sink area 400 mm²

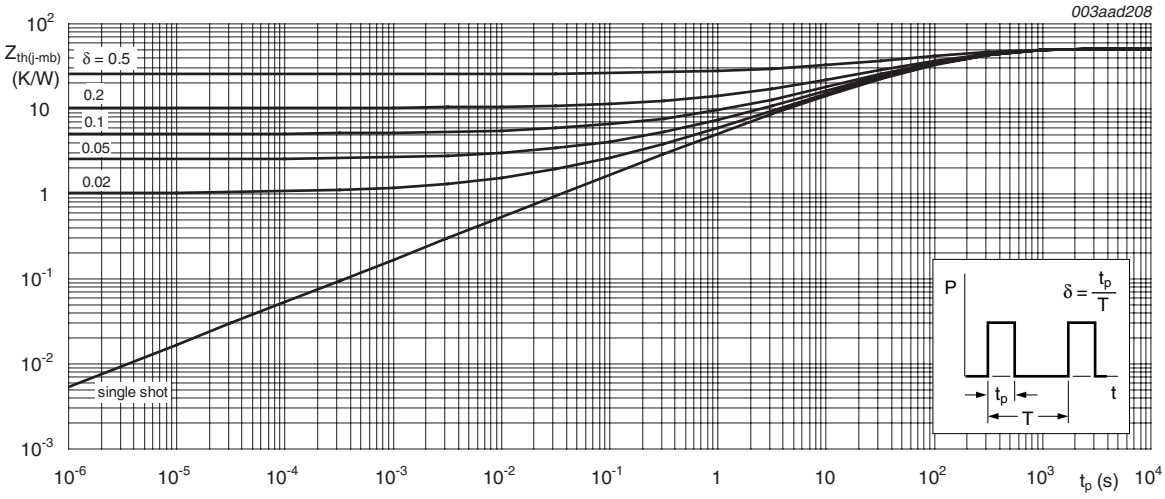


Fig 13. Transient thermal impedance from junction to ambient as a function of pulse duration, FET1 (PCB used for thermal tests; heat sink area 400mm²)

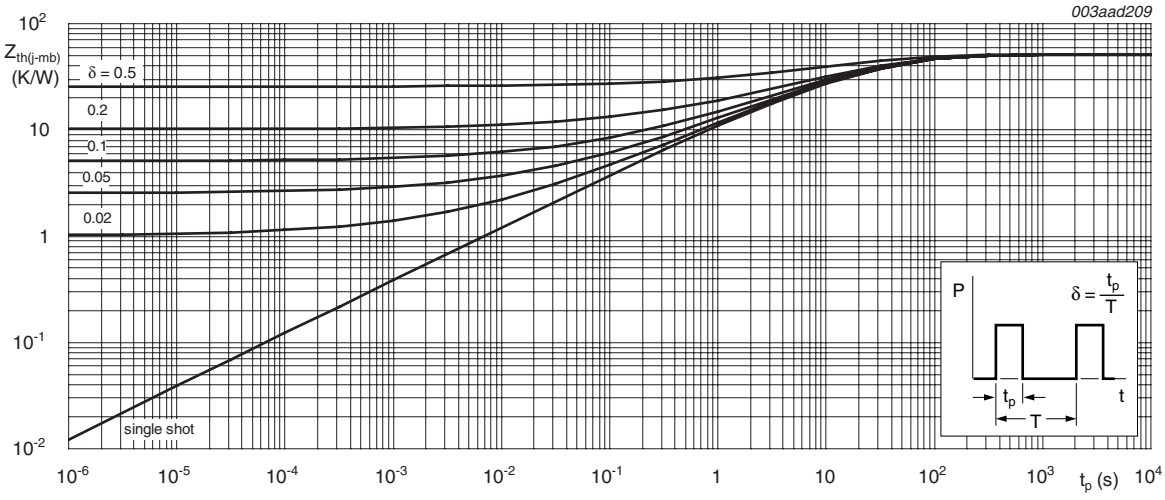


Fig 14. Transient thermal impedance from junction to ambient as a function of pulse duration, FET2 (PCB used for thermal tests; heat sink area 400mm²)

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics, FET1						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 21; see Figure 22	1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 21; see Figure 22	-	-	2.3	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 150 °C; see Figure 21; see Figure 22	0.5	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	3	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 150 °C	-	-	125	µA
I_{GSS}	gate leakage current	V_{DS} = 0 V; V_{GS} = 15 V; T_j = 25 °C	-	2	300	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 10 A; T_j = 25 °C; see Figure 23; see Figure 25	-	8.6	10	mΩ
		V_{GS} = 5 V; I_D = 10 A; T_j = 150 °C; see Figure 25; see Figure 23	-	-	18	mΩ
		V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 °C; see Figure 23; see Figure 25	-	9.4	11.1	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see Figure 23; see Figure 25	-	8.1	9	mΩ
I_D/I_{sense}	ratio of drain current to sense current	T_j = 25 °C; V_{GS} = 5 V; see Figure 27	8100	9000	9900	A/A
$S_{F(TSD)}$	temperature sense diode temperature coefficient	I_F = 250 µA; 25 °C < T_j < 150 °C; see Figure 29	-5.4	-5.7	-6	mV/K
$V_{F(TSD)}$	temperature sense diode forward voltage	I_F = 250 µA; T_j = 25 °C; see Figure 29	2.855	2.9	2.945	V
Static characteristics, FET2						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 21; see Figure 22	1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 21; see Figure 22	-	-	2.3	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 150 °C; see Figure 21; see Figure 22	0.5	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	3	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 150 °C	-	-	125	µA
I_{GSS}	gate leakage current	V_{DS} = 0 V; V_{GS} = 15 V; T_j = 25 °C	-	2	300	nA

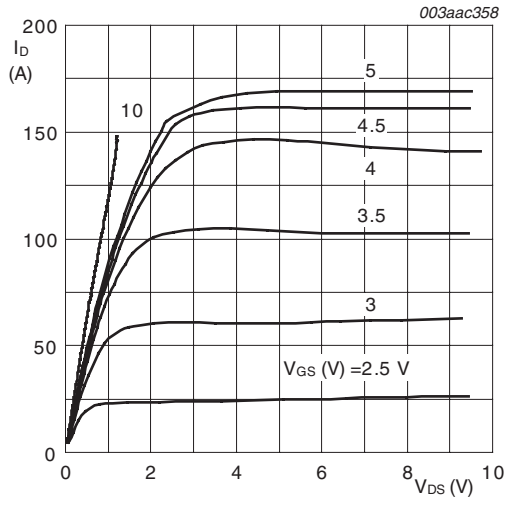
Table 6. Characteristics *...continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; see Figure 24; see Figure 26	-	21.3	25	mΩ
		V_{GS} = 5 V; I_D = 5 A; T_j = 150 °C; see Figure 24; see Figure 26	-	-	46.8	mΩ
		V_{GS} = 4.5 V; I_D = 5 A; T_j = 25 °C; see Figure 24; see Figure 26	-	23.7	27.9	mΩ
		V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; see Figure 24; see Figure 26	-	20.3	22.6	mΩ
I_D/I_{sense}	ratio of drain current to sense current	T_j = 25 °C; V_{GS} = 5 V; see Figure 28	5910	6570	7227	A/A
$S_{F(TSD)}$	temperature sense diode temperature coefficient	I_F = 250 µA; 25 °C < T_j < 150 °C; see Figure 29	-5.4	-5.7	-6	mV/K
$V_{F(TSD)}$	temperature sense diode forward voltage	I_F = 250 µA; T_j = 25 °C; see Figure 29	2.855	2.9	2.945	V
Dynamic characteristics, FET1						
$Q_{G(tot)}$	total gate charge	I_D = 10 A; V_{DS} = 44 V; V_{GS} = 5 V; see Figure 30	-	54	-	nC
Q_{GS}	gate-source charge		-	9.4	-	nC
Q_{GD}	gate-drain charge		-	21.5	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see Figure 32	-	3884	5178	pF
C_{oss}	output capacitance		-	540	648	pF
C_{rss}	reverse transfer capacitance		-	247	338	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 3 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 10 Ω	-	41	-	ns
t_r	rise time		-	94	-	ns
$t_{d(off)}$	turn-off delay time		-	184	-	ns
t_f	fall time		-	98	-	ns
L_D	internal drain inductance	From pin to centre of die	-	0.85	-	nH
L_S	internal source inductance	From source lead to source bonding pad	-	1.9	-	nH
Dynamic characteristics, FET2						
$Q_{G(tot)}$	total gate charge	I_D = 5 A; V_{DS} = 44 V; V_{GS} = 0 V; see Figure 31	-	23	-	nC
Q_{GS}	gate-source charge		-	3.4	-	nC
Q_{GD}	gate-drain charge		-	9	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see Figure 33	-	1736	2315	pF
C_{oss}	output capacitance		-	244	293	pF
C_{rss}	reverse transfer capacitance		-	119	163	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 6 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 10 Ω	-	29	-	ns
t_r	rise time		-	44	-	ns
$t_{d(off)}$	turn-off delay time		-	91	-	ns
t_f	fall time		-	46	-	ns

Table 6. Characteristics *...continued*

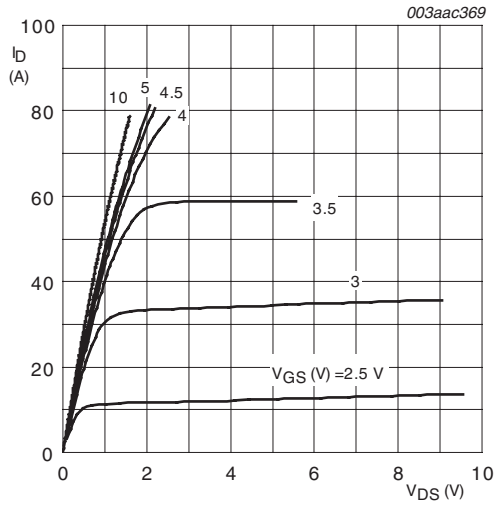
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
L_D	internal drain inductance	From pin to centre of die		-	0.85	-	nH
L_S	internal source inductance	From source lead to source bonding pad		-	2	-	nH
Source-drain diode, FET1							
V_{SD}	source-drain voltage	I_S = 10 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 34		-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 5 A; dI_S/dt = -100 A/µs; V_{GS} = -10 V; V_{DS} = 30 V;	[1]	-	66.4	-	ns
Q_r	recovered charge			-	126	-	nC
Source-drain diode, FET2							
V_{SD}	source-drain voltage	I_S = 5 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 35		-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 5 A; dI_S/dt = -100 A/µs; V_{GS} = -10 V; V_{DS} = 30 V		-	44	-	ns
Q_r	recovered charge			-	69	-	nC

[1] xsa



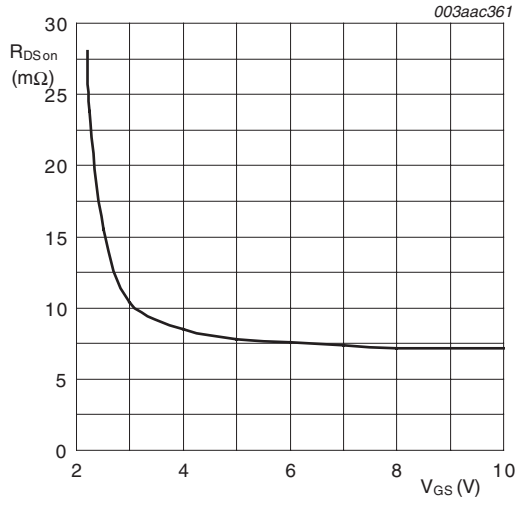
$T_j = 25\,°C; t_p = 300\,\mu s$

Fig 15. Output characteristics: drain current as a function of drain-source voltage; typical values, FET1



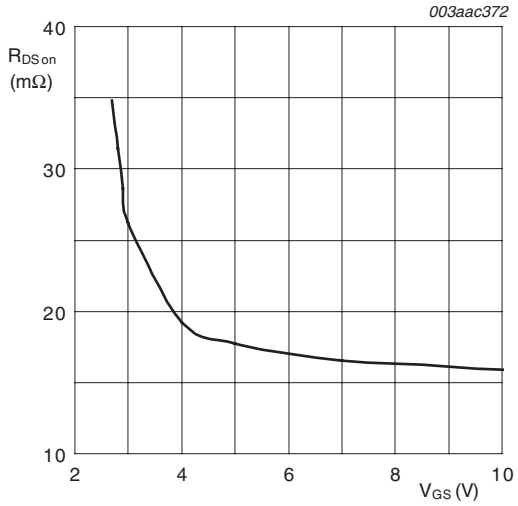
$T_j = 25\,°C; t_p = 300\,\mu s$

Fig 16. Output characteristics: drain current as a function of drain-source voltage; typical values, FET2



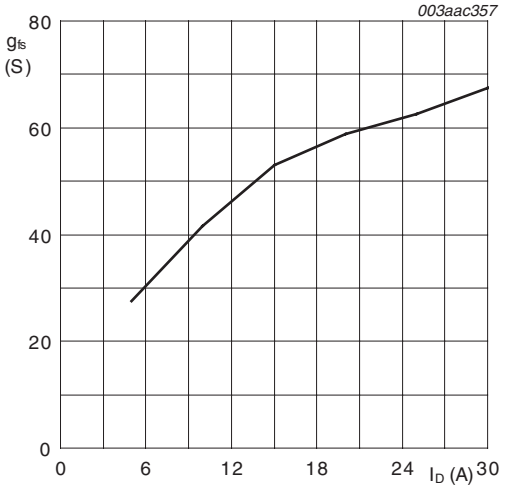
$T_j = 25\,°C; I_D = 10\,A$

Fig 17. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1



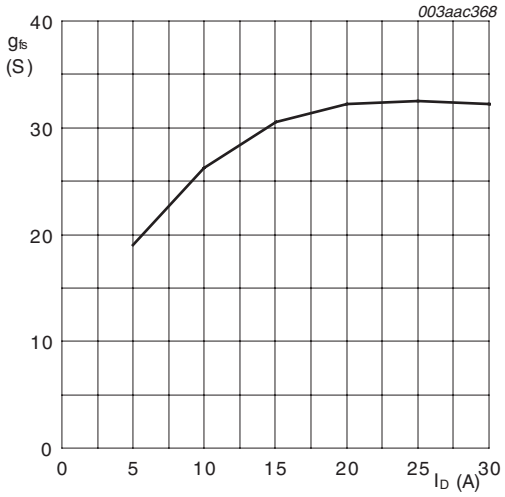
$T_j = 25\,°C; I_D = 10\,A$

Fig 18. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET2



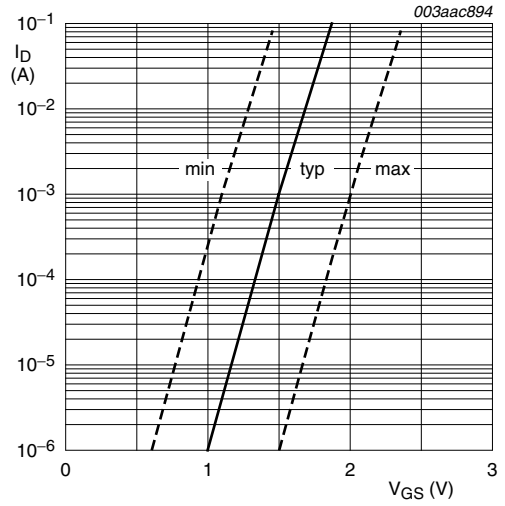
$T_j = 25\,°C; V_{DS} = 25\,V$

Fig 19. Forward transconductance as a function of drain current; typical values, FET1



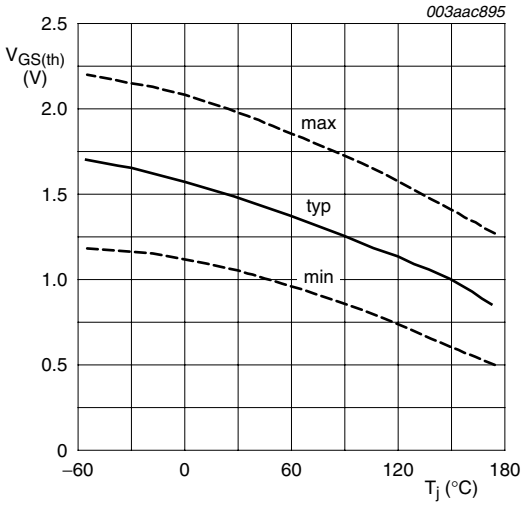
$T_j = 25\,°C; V_{DS} = 25\,V$

Fig 20. Forward transconductance as a function of drain current; typical values, FET2



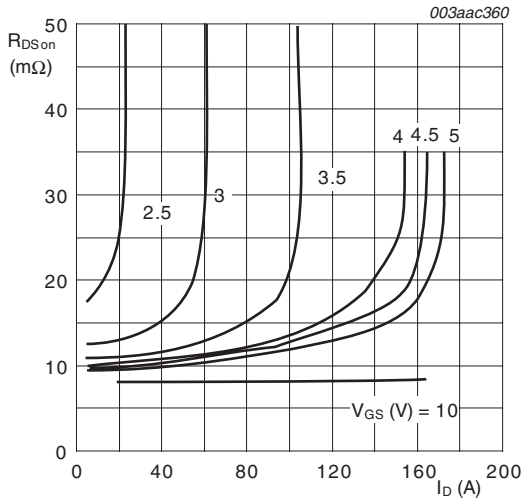
$T_j = 25\,°C; V_{DS} = V_{GS}$

Fig 21. Sub-threshold drain current as a function of gate-source voltage, FET1 and FET2



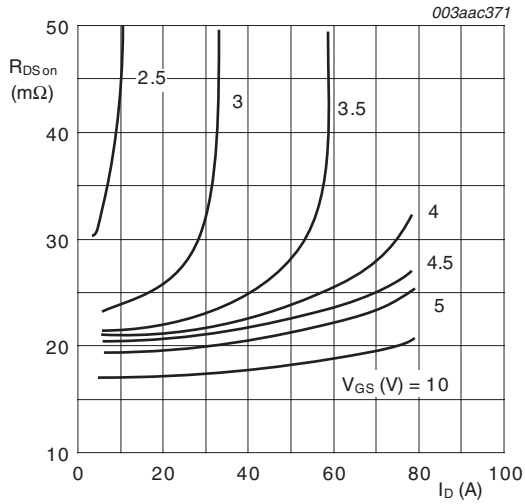
$I_D = 1\,mA; V_{DS} = V_{GS}$

Fig 22. Gate-source threshold voltage as a function of junction temperature, FET1 and FET2



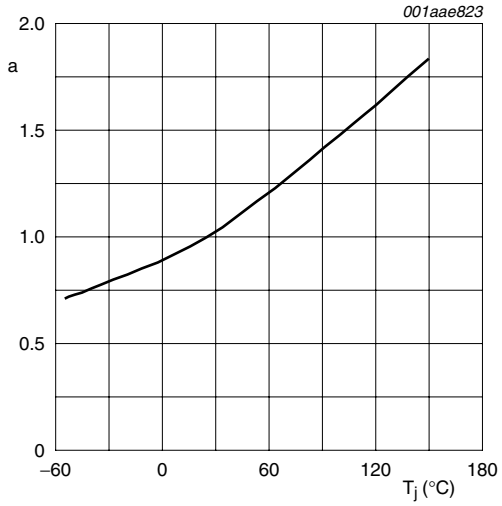
$T_j = 25\,°C; t_p = 300\,\mu s$

Fig 23. Drain-source on-state resistance as a function of drain current; typical values, FET1



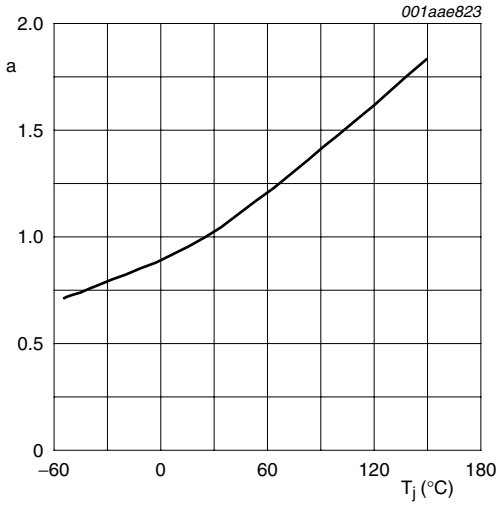
$T_j = 25\,°C; t_p = 300\,\mu s$

Fig 24. Drain-source on-state resistance as a function of drain current; typical values, FET2



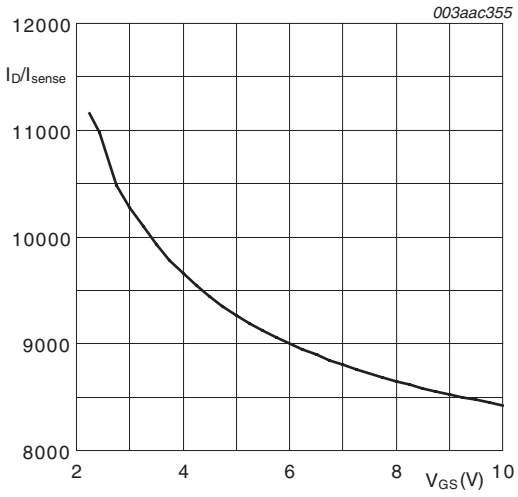
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 25. Normalized drain-source on-state resistance factor as a function of junction temperature, FET1



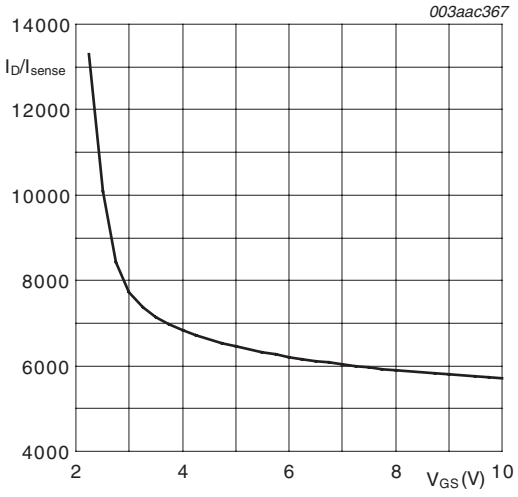
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 26. Normalized drain-source on-state resistance factor as a function of junction temperature, FET2



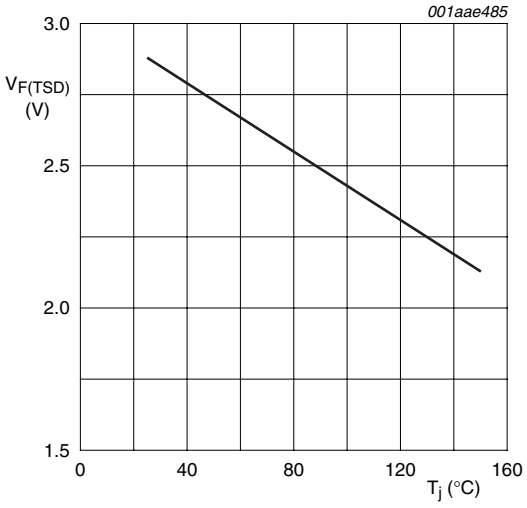
$T_j = 25\,°C; I_D = 5A$

Fig 27. Ratio of drain current to sense current as a function of gate-source voltage; typical values, FET1



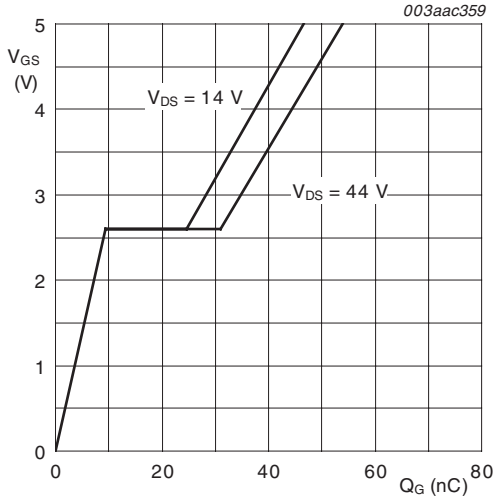
$T_j = 25\,°C; I_D = 5A$

Fig 28. Ratio of drain current to sense current as a function of gate-source voltage; typical values, FET2



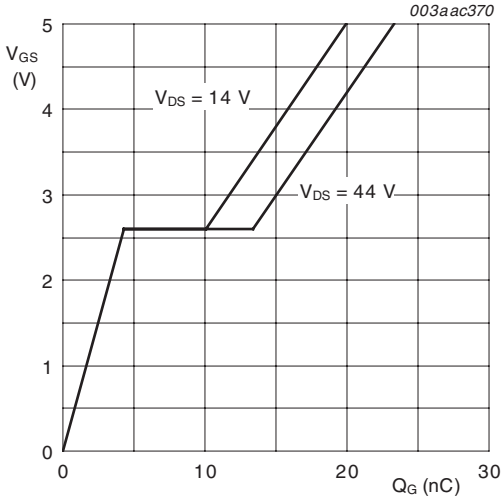
$I_F = 250\,\mu A$

Fig 29. Temperature sense diode forward voltage as a function of junction temperature; typical values, FET1 and FET2



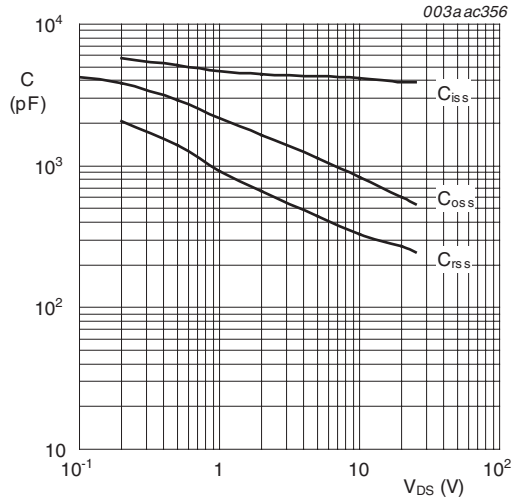
$T_j = 25\,°C; I_D = 10\,A$

Fig 30. Gate-source voltage as a function of turn-on gate charge; typical values, FET1



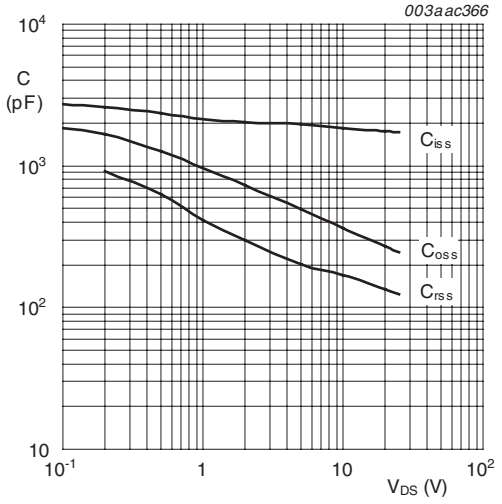
$T_j = 25\,°C; I_D = 10\,A$

Fig 31. Gate-source voltage as a function of turn-on gate charge; typical values, FET2



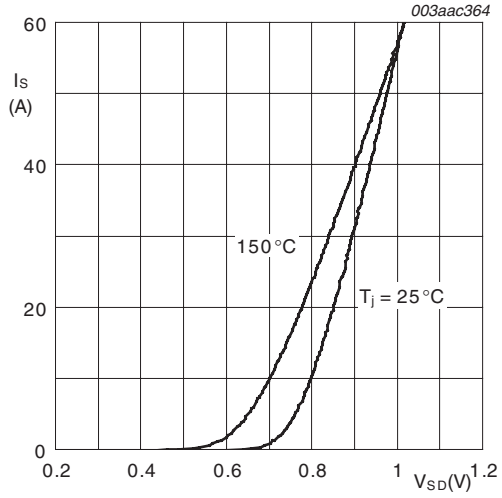
$V_{GS} = 0\,V; f = 1\,MHz$

Fig 32. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET1



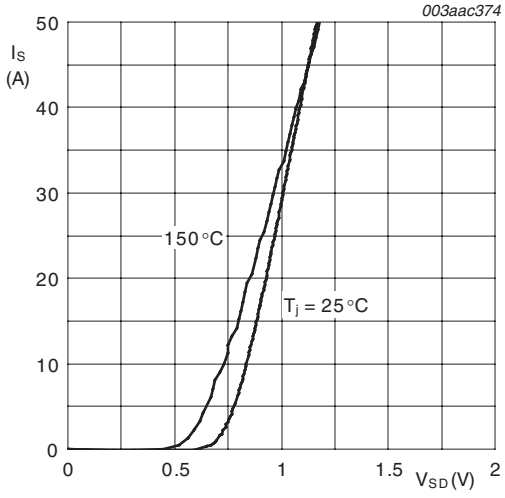
$V_{GS} = 0\,V; f = 1\,MHz$

Fig 33. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET2



$V_{GS} = 0\,V$

Fig 34. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET1

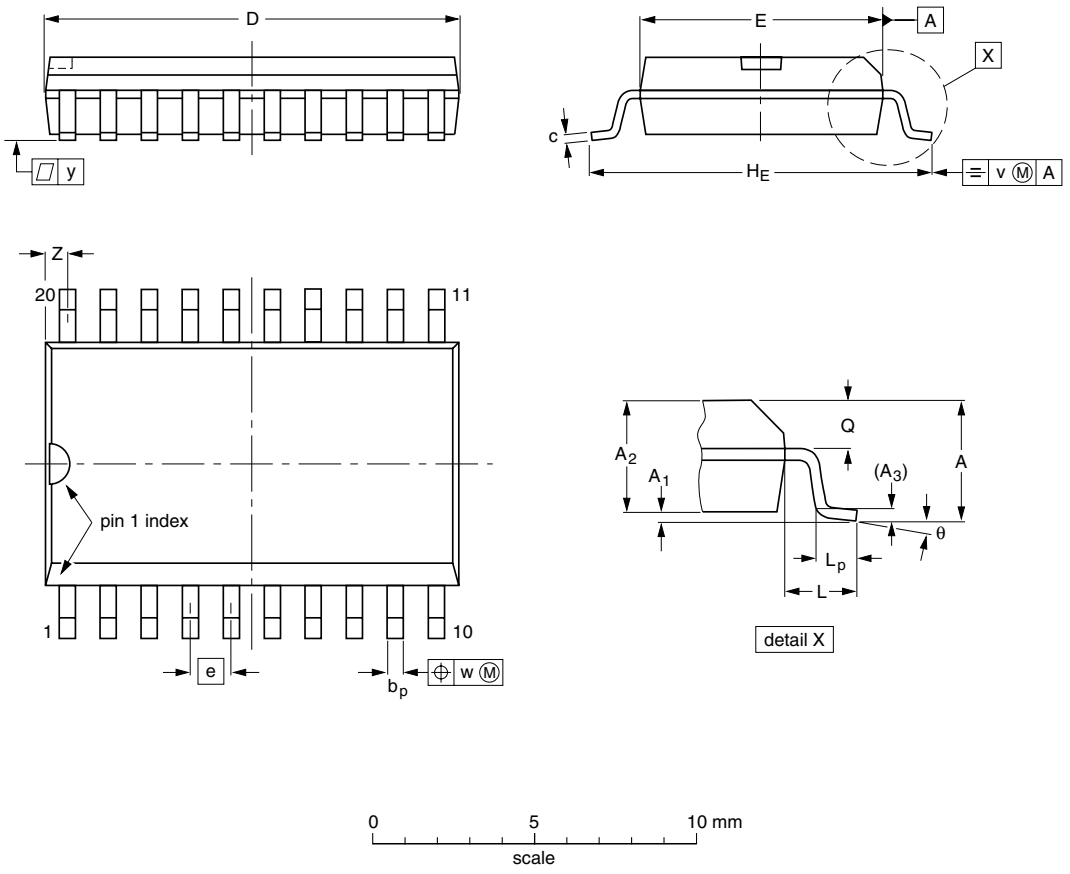


$V_{GS} = 0\,V$

Fig 35. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET2

7. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				~~99-12-27~~ 03-02-19

Fig 36. Package outline SOT163-1

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9MGP-55PTS_1	20090514	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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11. Contents

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